

AO3420

20V N-Channel MOSFET

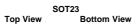
General Description

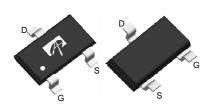
The AO3420 uses advanced trench technology to provide excellent $R_{\rm DS(ON)},$ low gate charge and operation with gate voltages as low as 1.8V while retaining a 12V $V_{\rm GS(MAX)}$ rating. This device is suitable for use as a uni-directional or bi-directional load switch.

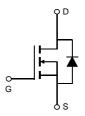
Product Summary

 $\begin{array}{lll} V_{DS} & 20V \\ I_D & (at \ V_{GS}{=}10V) & 6A \\ R_{DS(ON)} & (at \ V_{GS}{=}10V) & < 24m\Omega \\ R_{DS(ON)} & (at \ V_{GS}{=}4.5V) & < 27m\Omega \\ R_{DS(ON)} & (at \ V_{GS}{=}2.5V) & < 42m\Omega \\ R_{DS(ON)} & (at \ V_{GS}{=}1.8V) & < 55m\Omega \\ \end{array}$









Absolute Maximum Ratings T_A=25℃ unless otherwise noted

7 moonate manimum ramings 1 _A = 0 0 amoon 0 moon								
Parameter		Maximum	Units					
Drain-Source Voltage		20	V					
Gate-Source Voltage		±12	V					
T _A =25℃		6						
T _A =70℃	'D	5	A					
Pulsed Drain Current C		30						
T _A =25°C		1.4	W					
T _A =70℃	T'D	0.9	VV					
Junction and Storage Temperature Range		-55 to 150	C					
	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$ $T_{A}=25^{\circ}C$ $T_{A}=25^{\circ}C$	$ \begin{array}{c c} & & & & & & & \\ & & & & & & \\ & & & & $	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$					

Thermal Characteristics								
Parameter		Symbol	Тур	Max	Units			
Maximum Junction-to-Ambient A	t ≤ 10s	$R_{\theta JA}$	70	90	℃/W			
Maximum Junction-to-Ambient AD	Steady-State		100	125	C/W			
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	63	80	C/W			



Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Units			
STATIC PARAMETERS									
BV _{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu A, V_{GS}=0V$	20			V			
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V			1	μА			
		T _J =55℃			5				
I_{GSS}	Gate-Body leakage current	V_{DS} =0V, V_{GS} = ±12V			±100	nA			
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS} I_{D}=250\mu A$	0.4	0.75	1.1	V			
		V _{GS} =10V, I _D =6A		16	24	mΩ			
		T _J =125℃		23	35	11122			
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} =4.5V, I_D =5A		18	27	$m\Omega$			
		V_{GS} =2.5V, I_D =4A		23	42	$m\Omega$			
		V_{GS} =1.8V, I_D =2A		31	55	$m\Omega$			
g _{FS}	Forward Transconductance	V_{DS} =5V, I_{D} =6A		25		S			
V_{SD}	Diode Forward Voltage	I _S =1A,V _{GS} =0V		0.7	1	V			
Is	Maximum Body-Diode Continuous Current				2	Α			
DYNAMIC	PARAMETERS								
C _{iss}	Input Capacitance		420	525	630	pF			
C _{oss}	Output Capacitance	V _{GS} =0V, V _{DS} =10V, f=1MHz	65	95	125	pF			
C _{rss}	Reverse Transfer Capacitance		45	75	105	pF			
R_g	Gate resistance	V_{GS} =0V, V_{DS} =0V, f=1MHz	0.8	1.7	2.6	Ω			
SWITCHI	NG PARAMETERS								
Q _g (10V)	Total Gate Charge			12.5		nC			
Q _g (4.5V)	Total Gate Charge	V _{GS} =10V, V _{DS} =10V, I _D =6A		6		nC			
Q_{gs}	Gate Source Charge	V _{GS} =10V, V _{DS} =10V, I _D =0A		1		nC			
Q_{gd}	Gate Drain Charge			2		nC			
t _{D(on)}	Turn-On DelayTime			3		ns			
t _r	Turn-On Rise Time	V_{GS} =10V, V_{DS} =10V, R_L =1.7 Ω ,		7.5		ns			
t _{D(off)}	Turn-Off DelayTime	$R_{GEN}=3\Omega$		20		ns			
t _f	Turn-Off Fall Time]		6		ns			
t _{rr}	Body Diode Reverse Recovery Time	I _F =6A, dI/dt=100A/μs		14		ns			
Q _{rr}	i	I _F =6A, dI/dt=100A/μs		6		nC			

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The value in any given application depends on the user's specific board design. B. The power dissipation P_D is based on $T_{J(MAX)}$ =150° C, using \leq 10s junction-to-ambient thermal resistance.

THIS PRODUCT HAS BEEN DESIGNED AND QUALIFIED FOR THE CONSUMER MARKET. APPLICATIONS OR USES AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150° C. Ratings are based on low frequency and duty cycles to keep initial T_J =25° C.

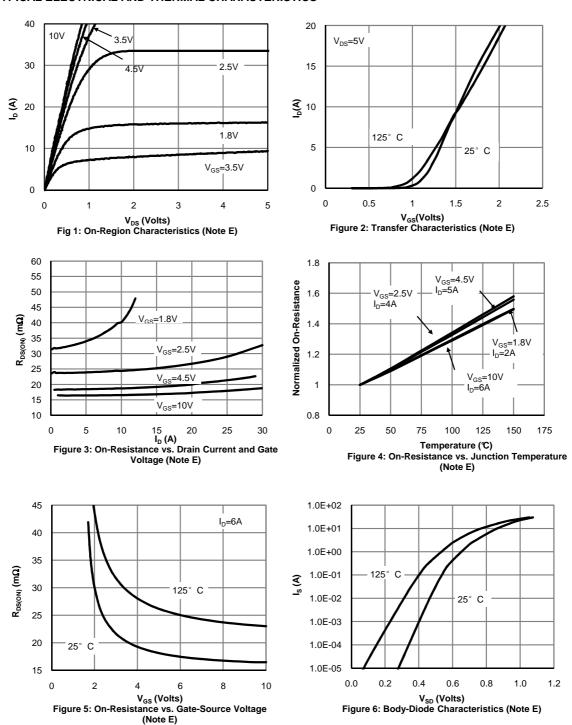
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-ambient thermal impedence which is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, assuming a maximum junction temperature of $T_{J(MAX)}$ =150° C. The SOA curve provides a single pulse rating.

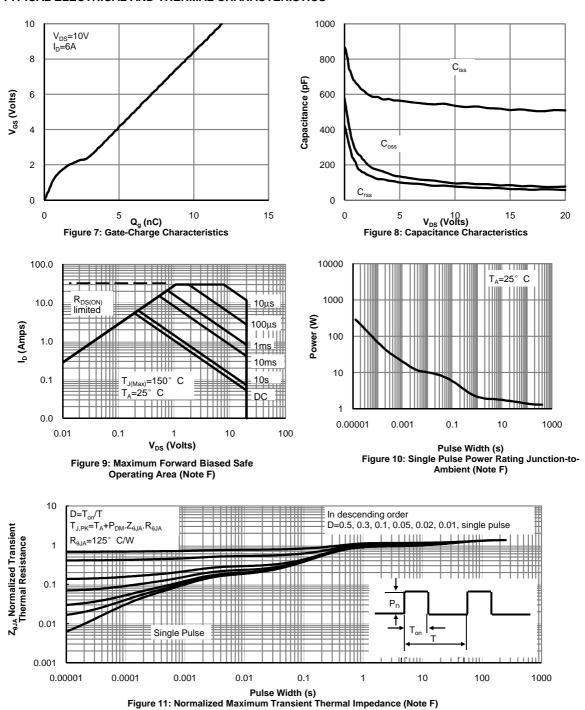


TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



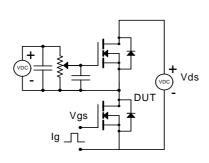


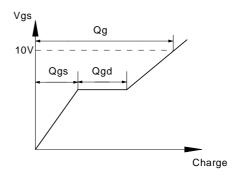
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



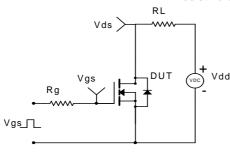


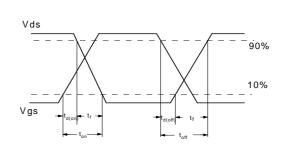
Gate Charge Test Circuit & Waveform



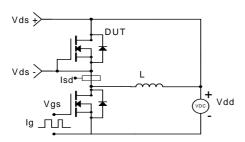


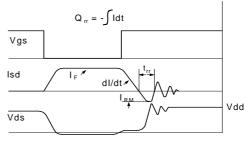
Resistive Switching Test Circuit & Waveforms





Diode Recovery Test Circuit & Waveforms





X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for alpha & omega manufacturer:

Other Similar products are found below:

AOT1608L AO4492 AOD478 AOD468 AOZ6135HI AO5404E AOD482 AO3402 AOTF10B60D AOU3N50 AOZ1235QI-01

AOK42S60L AON7534 AOD3N50 AO4468 AO3401A AO3415 AON2403 AOD4130 AOB290L AOTF42S60L AOTF190A60L

AO4404B AON6756 AO4813 AO3414 aot412 AO4818 AOT270AL AO6420 AO3442 AOT2918L AO4616 AO4294 AOZ1020AI

AON6250 AON6444 AOZ3011PI AO8820 AOT10N65 AOK20S60L AOK20N60L AON6548 AO3415A AOT470 AOZ8905CI

AOK60N30L AOT410L AON6280 AON6414A